

ABSTRACT OF THE DISCLOSURE

A semiconductor device is disclosed. The device includes a semiconductor region and P-type and N-type diffusion layers formed in the semiconductor region.

5 The semiconductor region includes a germanium low-concentration region containing germanium of low concentration and a germanium high-concentration region containing germanium of high concentration. A boundary region between the P-type and N-type diffusion layers
10 lies in the germanium high-concentration region.

A silicide film is formed to extend from the P-type diffusion layer over to the boundary region and the N-type diffusion layer.